L	Hits	Search Text	DB	Time stamp
Number				
1	14	(measuring with (pattern adj density))	USPAT;	2004/09/08
		and (polishing or polish or CMP)	US-PGPUB	15:47
2	6	((measuring with (pattern adj density))	USPAT;	2004/09/08
		and (polishing or polish or CMP)) and	US-PGPUB	15:49
		@ad<20010831		
3	0	(measuring with (pattern adj density))	EPO; JPO;	2004/09/08
		and (polishing or polish or CMP)	DERWENT;	15:47
			IBM_TDB	
5	94	438/692-695.ccls. and (pattern adj	USPAT;	2004/09/08
		density) and (polishing or polish or CMP)	US-PGPUB	15:49
6	66	(438/692-695.ccls. and (pattern adj	USPAT;	2004/09/08
		density) and (polishing or polish or	US-PGPUB	15:49
		CMP)) and @ad<20010831		
7	17	((438/692-695.ccls. and (pattern adj	USPAT;	2004/09/08
		density) and (polishing or polish or	US-PGPUB	15:50
		CMP)) and @ad<20010831) and measuring		

DOCUMENT-IDENTIFIER: US 20010036676 A1

TITLE: Semiconductor wafer polishing

endpoint detecting system

and method therefor

----- KWIC -----

Summary of Invention Paragraph - BSTX (6):

[0005] FIG. 10 is an illustration showing a construction of one example of

the prior art. A semiconductor wafer polishing endpoint detecting system shown

in FIG. 10 is constructed with a polishing bed 2 provided with a predetermined

dimension of detection hole 43, an abrasive cloth 3 on the polishing bed 2 and

provided with a detection hole 43 at the same position as the polishing bed 2,

a view window 44 sealing the detection hole 43 as polishing fluid in-flow

preventing means for preventing in-flow of a polishing fluid into a detection

optical system from the detection hole 43, a laser light source 46 for

irradiating an inspection light 45 of a predetermined diameter onto a polishing

surface of the wafer as a polishing object through the detection hole 43 and

the view window 44, a photodetector 48 receiving a regular reflection light 47

reflected on the wafer for measuring a light amount to
output as a light amount

signal o, averaging means 49 for averaging the light amount signal o per one

turn of the wafer 1 and outputting a third averaged data pin discrete manner,

and polishing end point detection means 50 comparing the averaged data p output

from the averaging means 40 with a predetermined threshold value detected by a

reflection index of a material formed on the wafer 1, pattern density and a

structure of the wafer 1, such as pattern density or the

like and detecting a timing when the averaged data p is decreased below the threshold value as the polishing endpoint.